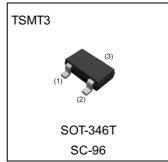


#### Medium power transistor (60V, 2A)

Parameter	Value	
$V_{CEO}$	60V	
Ic	2A	

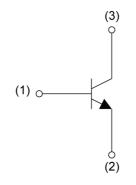
### Outline



#### Features

- 1)High speed switching. (t<sub>f</sub>:Typ.:35ns at I<sub>C</sub>=2A)
- 2)Low saturation voltage, typically (Typ.:200mV at I<sub>C</sub>=1.0A, I<sub>B</sub>=100mA)
- 3)Storong discharge power for inductive load and capacitance load.
- 4)Complements the 2SA2094

### •Inner circuit



- (1) Base
- (2) Emitter
- (3) Collector

#### Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

#### Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SC5866	TSMT3	2928	TL	180	8	3000	VL

# • Absolute maximum ratings $(T_a = 25^{\circ}C)$

Parameter	Symbol	Values	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	60	V
Emitter-base voltage	$V_{EBO}$	6	V
Calla star a commant	I <sub>C</sub>	2	Α
Collector current	I <sub>CP</sub> *1	4	Α
Power dissipation	P <sub>D</sub> *2	0.5	W
Junction temperature	Tj	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 100μA	60	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	60	-	ı	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 100μA	6	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V	-	-	1.0	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	1.0	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 100mA	-	200	500	mV
DC current gain	h <sub>FE</sub>	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	120	-	390	-
Transition frequency	f <sub>T</sub> *3	$V_{CE} = 10V, I_{E} = -100mA,$ f = 10MHz	-	200	-	MHz
Output capacitance	C <sub>ob</sub>	$V_{CB} = 10V$ , $I_E = 0A$ , $f = 1MHz$	-	10	-	pF
Turn-On time	t <sub>on</sub> *3	I <sub>C</sub> = 2A, I <sub>B1</sub> = 200mA,	-	50	-	ns
Storage time	t <sub>stg</sub> *3	$I_{B2} = -200 \text{mA},$ $V_{CC} \approx 25 \text{V},$	-	120	-	ns
Fall time	t <sub>f</sub> *3	$R_L = 12.5\Omega$ See test circuit	-	35		ns

### hFE values are calssified as follows:

rank	Q	R	-	-	-
hFE	120-270	180-390	-	-	-

<sup>\*1</sup> Pw=10ms

<sup>\*2</sup> Each terminal mounted on a reference land.

<sup>\*3</sup> Pulsed

# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

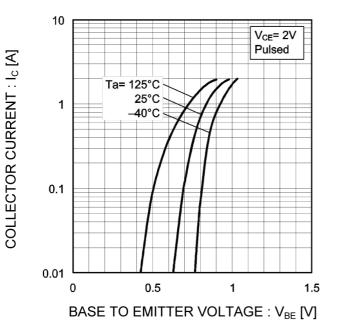
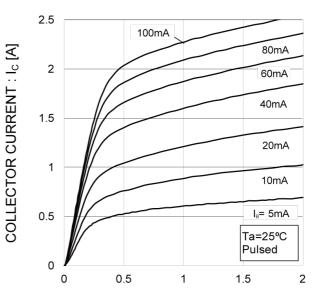


Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE :  $V_{\text{CE}}\left[V\right]$ 

Fig.3 DC Current Gain vs. Collector Current (I)

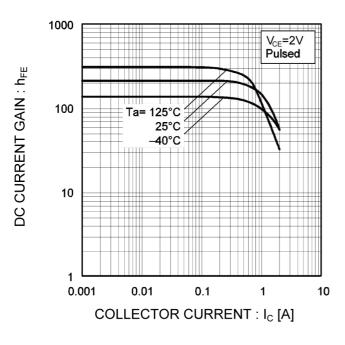
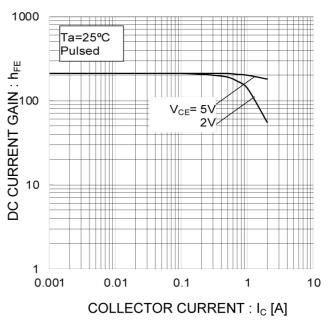


Fig.4 DC Current Gain vs. Collector Current (II)



# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

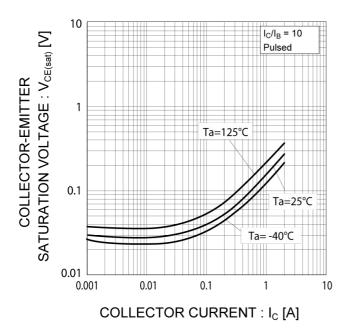


Fig.6 Collector-Emitter Saturation
Voltage vs. Collector Current (II)

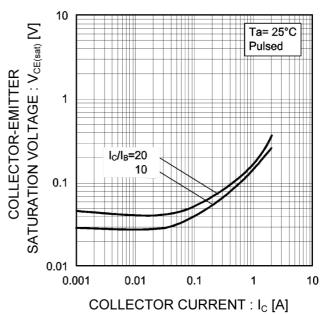


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

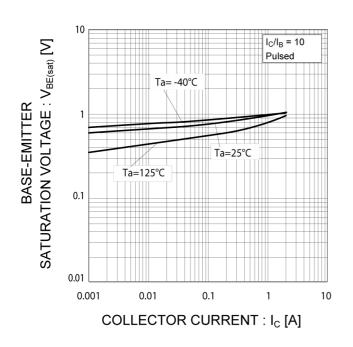
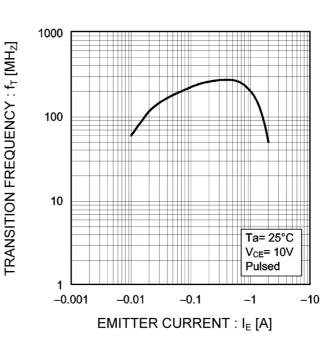


Fig.8 Gain Bandwidth Product vs. Emitter Current



## ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.9 Collector Output Capacitance vs. Collector-Base Voltage

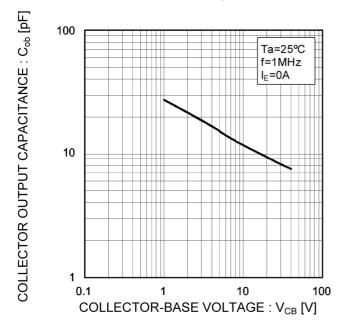
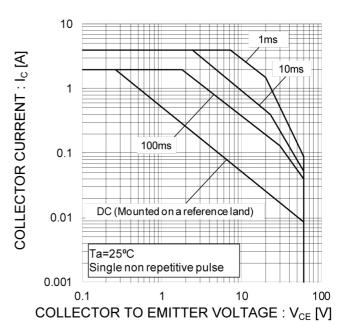
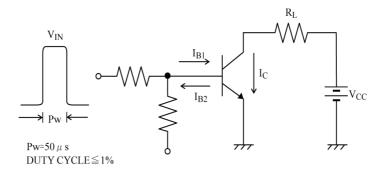
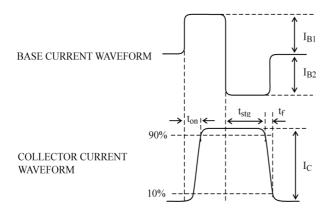


Fig.10 Safe Operating Area



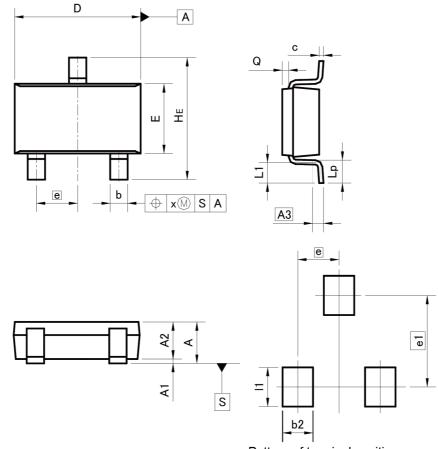
#### SWITCHING TIME TEST CIRCUIT





#### Dimensions

TSMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	I	1.00	-	0.039	
A1	0.00	0.10	0.000	0.004	
A2	0.75	0.95	0.030	0.037	
A3	0.5	25	0.010		
b	0.35	0.50	0.014	0.020	
С	0.10	0.26	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	0.95		37	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.05	0.25	0.002	0.010	
Х	-	0.20	-	0.008	

	DIM	MILIMETERS		INCHES		
	DIM	MIN	MAX	MIN	MAX	
	b2		0.70	-	0.028	
	e1	2.	10	0.0	83	
	11	ı	0.90	ı	0.035	

Dimension in mm/inches



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